

**isc Silicon PNP Power Transistors**

**BUX66B/C**

**DESCRIPTION**

- Continuous Collector Current- $I_C = -2A$
- Power Dissipation- $P_D = 35W @ T_C = 25^\circ C$
- Collector-Emitter Saturation Voltage-  
:  $V_{CE(sat)} = -2.5V(Max) @ I_C = -1A$
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

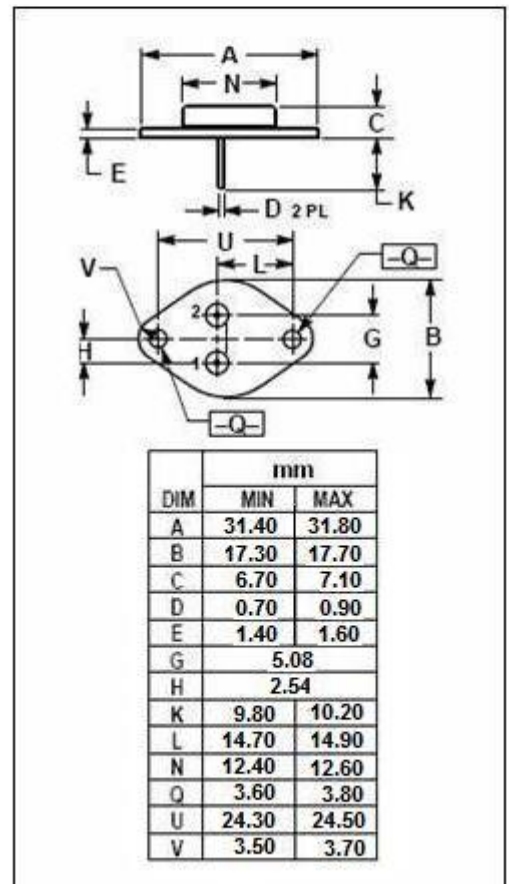
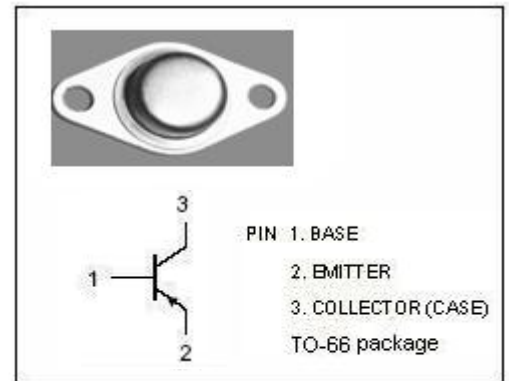
- Designed for high-speed switching and linear amplifier application for high-voltage operational amplifiers, switching regulators, converters, deflection stages and high fidelity amplifiers.

**ABSOLUTE MAXIMUM RATINGS( $T_a = 25^\circ C$ )**

SYMBOL	PARAMETER	VALUE	UNIT	
$V_{CBO}$	Collector-Base Voltage	BUX66B	-350	V
		BUX66C	-400	
$V_{CEO}$	Collector-Emitter Voltage	BUX66B	-300	V
		BUX66C	-350	
$V_{EBO}$	Emitter-Base Voltage	-6	V	
$I_C$	Collector Current-Continuous	-2.0	A	
$I_{CP}$	Collector Current-Peak	-5.0	A	
$I_B$	Base Current	-1.0	A	
$P_C$	Collector Power Dissipation@ $T_C = 25^\circ C$	35	W	
$T_J$	Junction Temperature	200	$^\circ C$	
$T_{stg}$	Storage Temperature	-65~200	$^\circ C$	

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance, Junction to Case	5.0	$^\circ C/W$



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**ELECTRICAL CHARACTERISTICS**

 T<sub>C</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	BUX66B	I <sub>C</sub> = -50mA ; I <sub>B</sub> =0	-300			V
		BUX66C		-350			
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage		I <sub>C</sub> = -1A; I <sub>B</sub> = -0.15A			-2.5	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage		I <sub>C</sub> = -1A; I <sub>B</sub> = -0.15A			-1.5	V
I <sub>CEO</sub>	Collector Cutoff Current		V <sub>CE</sub> = -150V; I <sub>B</sub> = 0			-5.0	mA
I <sub>CBO</sub>	Collector Cutoff Current	BUX66B	V <sub>CB</sub> =-350V; I <sub>E</sub> =0; V <sub>CB</sub> =-350V; I <sub>E</sub> =0; T <sub>C</sub> =100°C			-8.0 -10.0	mA
		BUX66C	V <sub>CB</sub> =-400V; I <sub>E</sub> =0; V <sub>CB</sub> =-400V; I <sub>E</sub> =0; T <sub>C</sub> =100°C			-8.0 -10.0	
I <sub>EBO</sub>	Emitter Cutoff Current		V <sub>EB</sub> = -6V; I <sub>C</sub> =0			-1.0	mA
h <sub>FE</sub>	DC Current Gain		I <sub>C</sub> = -1A; V <sub>CE</sub> = -5V	10		150	

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